SiC JFET Division

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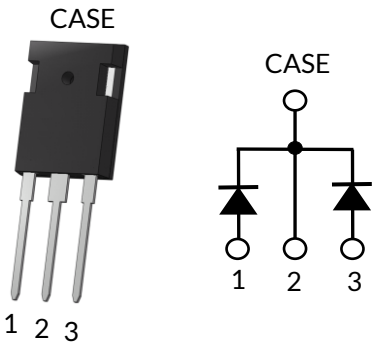
DATASHEET

UJ3D1220KSD



Part Number	Package	Marking
UJ3D1220KSD	TO-247-3L	UJ3D1220KSD

Silicon Carbide (SiC) Diode - EliteSiC, TO-247-3L, 20 A, 1200 V SiC Merged PiN-Schottky (MPS) Dual Diode

Rev. D, Jan 2025

Description

UnitedSiC offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.

Features

- Maximum operating temperature of 175°C
- Easy paralleling
- Extremely fast switching not dependent on temperature
- No reverse or forward recovery
- Enhanced surge current capability, MPS structure
- Excellent thermal performance, Ag sintered
- 100% UIS tested
- AEC-Q101 qualified

Typical applications

- Power converters
- Industrial motor drives
- Switch mode power supplies
- Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value (Leg/Device)	Units
DC blocking voltage	V_R		1200	V
Repetitive peak reverse voltage, T_J=25°C	V_{RRM}		1200	V
Surge peak reverse voltage	V_{RSM}		1200	V
Maximum DC forward current	I_F	T_C = 158°C	10/20	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	T_C = 25°C, t_p = 10ms	120/240	A
		T_C = 110°C, t_p = 10ms	110/220	
Repetitive forward surge current sine halfwave, D=0.1	I_{FRM}	T_C = 25°C, t_p = 10ms	56.7/113.4	A
		T_C = 110°C, t_p = 10ms	33.6/67.2	
Non-repetitive peak forward current	$I_{F,max}$	T_C = 25°C, t_p = 10µs	720/1440	A
		T_C = 110°C, t_p = 10µs	720/1440	
i^2t value	$\int i^2dt$	T_C = 25°C, t_p = 10ms	72/288	A^2s
		T_C = 110°C, t_p = 10ms	60/240	
Power dissipation	P_{tot}	T_C = 25°C	234.4/468.8	W
		T_C = 158°C	26.6/53.2	
Maximum junction temperature	$T_{J,max}$		175	°C
Operating and storage temperature	T_J, T_{STG}		-55 to 175	°C
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	°C

Thermal Characteristics

Parameter	Symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Thermal resistance, junction-to-case	$R_{\theta JC}$			0.49/0.245	0.64/0.32	°C/W

Electrical Characteristics (T_J = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Forward voltage	V_F	I_F=10A/20A, T_J=25°C	-	1.4	1.6	V
		I_F=10A/20A, T_J=150°C	-	1.85	2.3	
		I_F=10A/20A, T_J=175°C	-	2	2.6	
Reverse current	I_R	V_R=1200V, T_J=25°C	-	10/20	110/220	µA
		V_R=1200V, T_J=175°C	-	450/900		
Total capacitive charge (1)	Q_C	V_R=800V		51/102		nC
Total capacitance	C	V_R=1V, f = 1MHz		510/1020		pF
		V_R=400V, f = 1MHz		48/96		
		V_R=800V, f = 1MHz		41/82		
Capacitance stored energy	E_C	V_R=800V		15/30		µJ

(1) Q_c is independent on T_J, di_F/dt, and I_F as shown in the application note USCi_AN0011.

Typical Performance Diagrams (Per Leg)

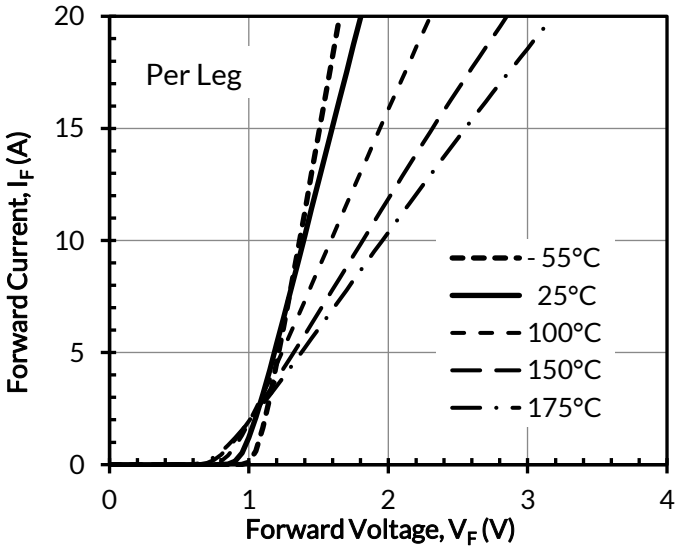


Figure 1. Typical forward characteristics

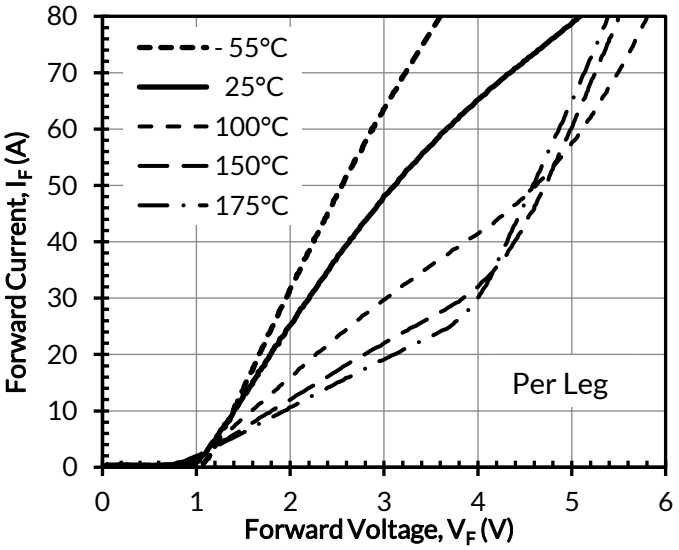


Figure 2. Typical forward characteristics in surge current

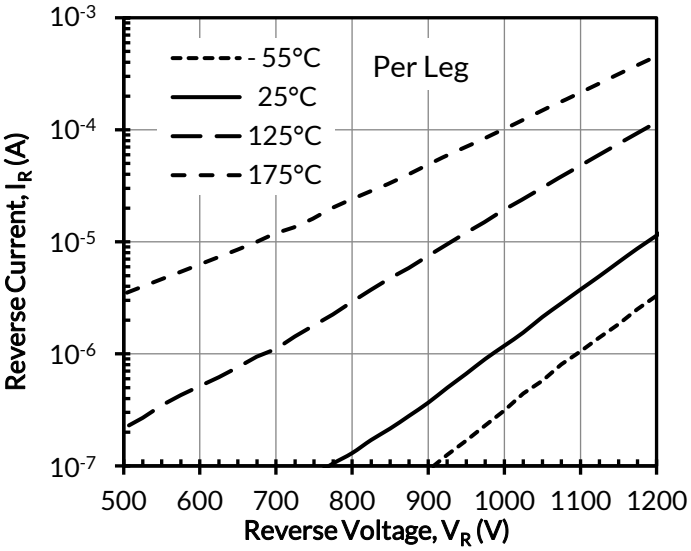


Figure 3. Typical reverse characteristics

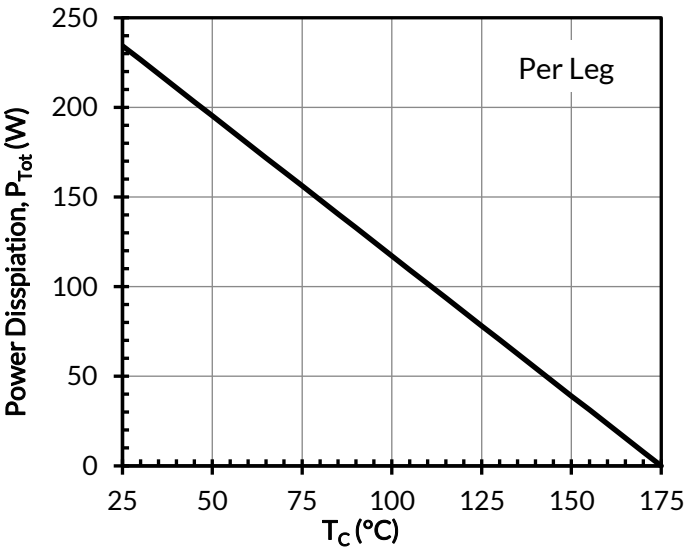


Figure 4. Power dissipation

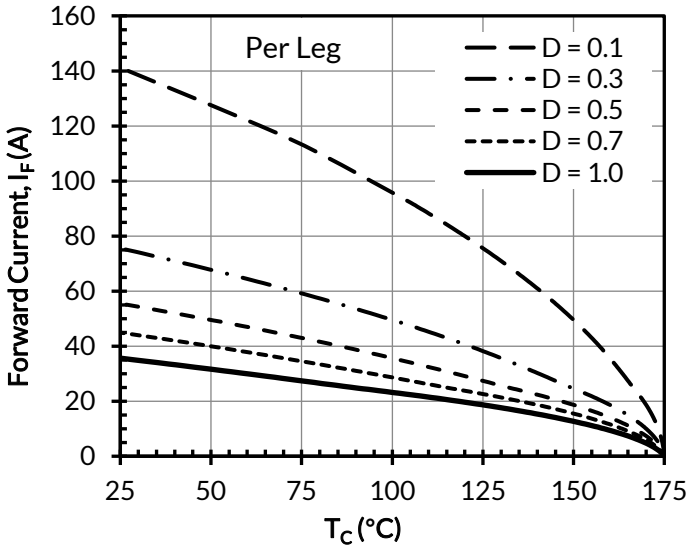


Figure 5. Diode forward current

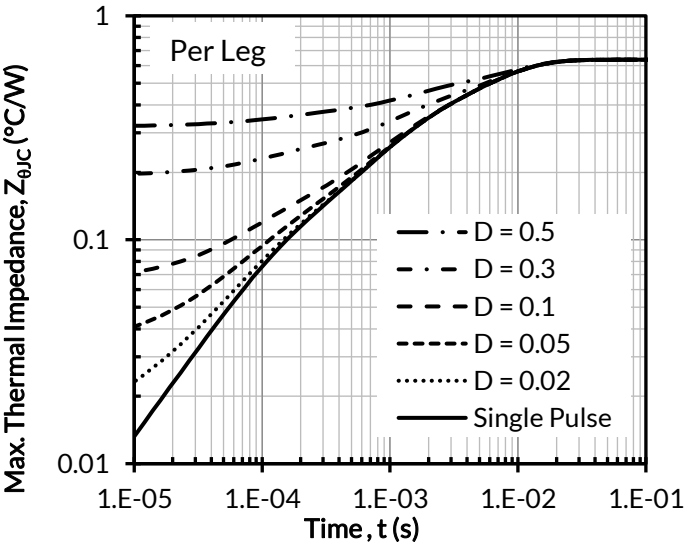


Figure 6. Maximum transient thermal impedance

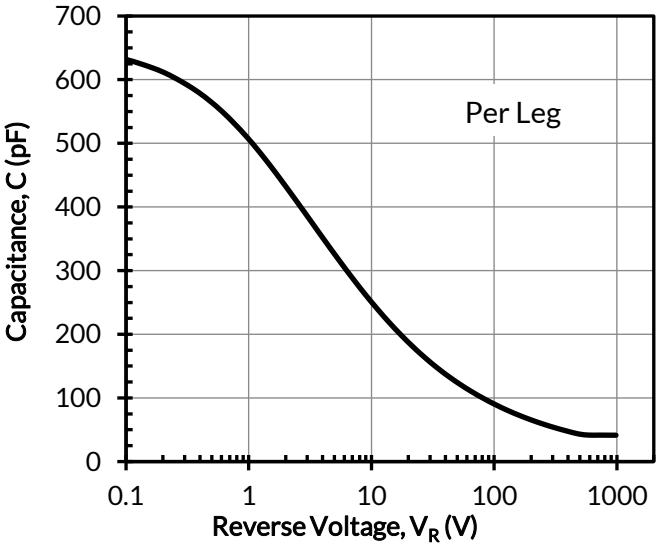


Figure 7. Capacitance vs. reverse voltage at 1MHz

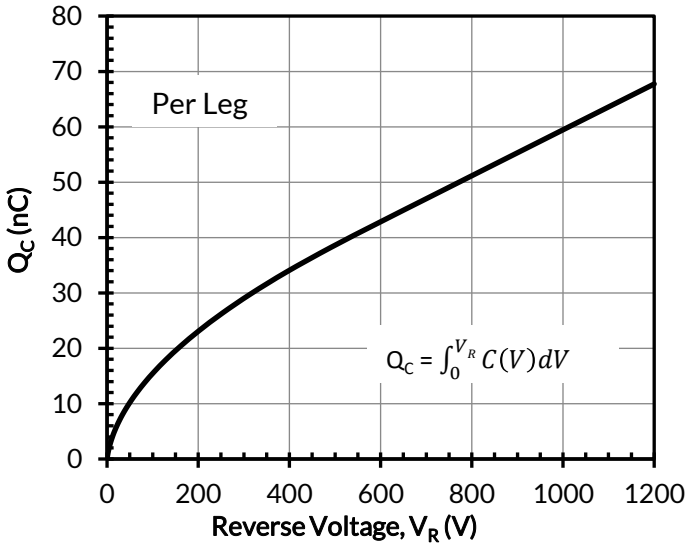


Figure 8. Typical capacitive charge vs. reverse voltage

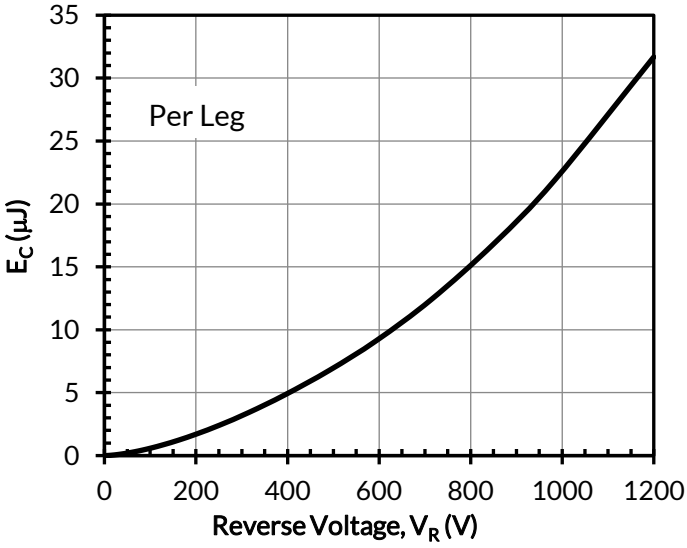


Figure 9. Typical capacitance stored energy vs. reverse voltage

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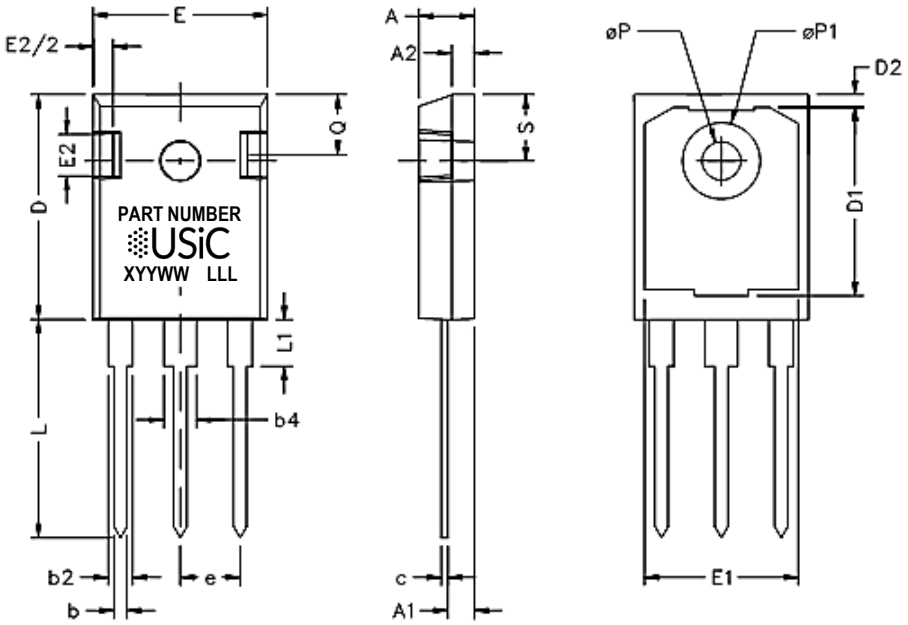
TO-247-3L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

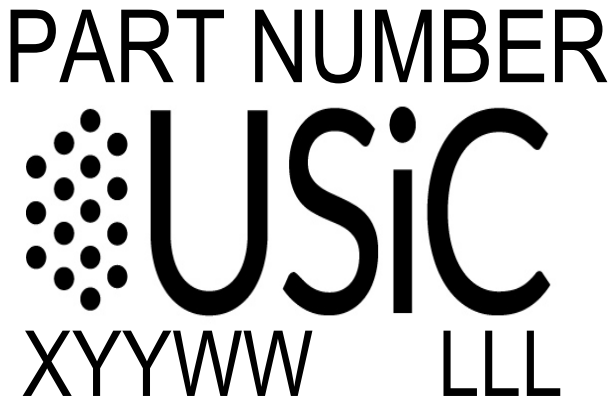
PACKAGE OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.185	0.209	4.699	5.309
A1	0.087	0.102	2.21	2.61
A2	0.059	0.098	1.499	2.489
b	0.039	0.055	0.991	1.397
b2	0.065	0.094	1.651	2.388
b4	0.102	0.135	2.591	3.429
c	0.015	0.035	0.381	0.889
D	0.819	0.845	20.803	21.463
D1	0.515	-	13.081	-
D2	0.02	0.053	0.508	1.346
E	0.61	0.64	15.494	16.256
e	0.214 BSC		5.44 BSC	
E1	0.53	-	13.462	-
E2	0.135	0.157	3.429	3.988
L	0.78	0.8	19.812	20.32
L1	-	0.177	-	4.496
ØP	0.14	0.144	3.556	3.658
ØP1	0.278	0.291	7.061	7.391
Q	0.212	0.244	5.385	6.198
S	0.243 BSC		6.17 BSC	

TO-247-3L PACKAGE OUTLINE, PART MARKING AND TUBE SPECIFICATIONS

PART MARKING



PART NUMBER = REFER TO DS_PN DECODER FOR DETAILS

X = ASSEMBLY SITE
YY = YEAR
WW = WORK WEEK
LLL = LOT ID

PACKING TYPE

ANTI-STATIC TUBE

QUANTITY /TUBE : 30 UNITS

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